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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Bao, *et al.* Docket No.: TSM03-0927
Serial No.: 10/800,510 Art Unit: 2818
Filed: March 15, 2004 Examiner: Tu-Tu Ho
For: Semiconductor Device Having a Second Level of Metallization Formed
over a First Level with Minimal Damage to the First Level and Method

Mail Stop: Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

Dear Sir:

The following amendments and remarks are presented in response to the Examiner's

Office Action mailed August 3, 2005. Please amend the above-referenced application as follows.